SEMICONDUCTOR

# FAN7384 Half-Bridge Gate-Drive IC

### Features

- Floating Channel for Bootstrap Operation to +600V
- Typically 250mA/500mA Sourcing/Sinking Current Driving Capability for Both Channels
- Extended Allowable Negative V<sub>S</sub> Swing to -9.8V for Signal Propagation at V<sub>DD</sub>=V<sub>BS</sub>=15V
- Matched Propagation Delay Below 50ns
- Output In-Phase with Input Signal
- 3.3V and 5V Input Logic Compatible
- Built-in Shoot-Through Prevention Logic
- Built-in Common Mode dv/dt Noise Canceling Circuit
- Built-in UVLO Functions for Both Channels
- Built-in Cycle-by-Cycle Shutdown Function
- Built-in Soft-Off Function
- Built-in Bi-Directional Fault Function
- Built-in Short-Circuit Protection Function

# Applications

- Motor Inverter Driver
- Normal Half-Bridge and Full-Bridge Driver
- Switching Mode Power Supply

### Description

The FAN7384 is a monolithic half-bridge gate-drive IC designed for high voltage, high speed driving MOSFETs and IGBTs operating up to +600V.

Fairchild's high-voltage process and common-mode noise canceling technique provide stable operation of high-side drivers under high-dv/dt noise circumstances.

An advanced level-shift circuit allows high-side gate driver operation up to  $V_{\rm S}$  = -9.8V (typical) for  $V_{\rm BS}$  =15V.

The UVLO circuits prevent malfunction when  $V_{\text{DD}}$  and  $V_{\text{BS}}$  are lower than the specified threshold voltage.

Output drivers typically source/sink 250mA/500mA, respectively, which is suitable for half-bridge and fullbridge applications in motor drive systems.

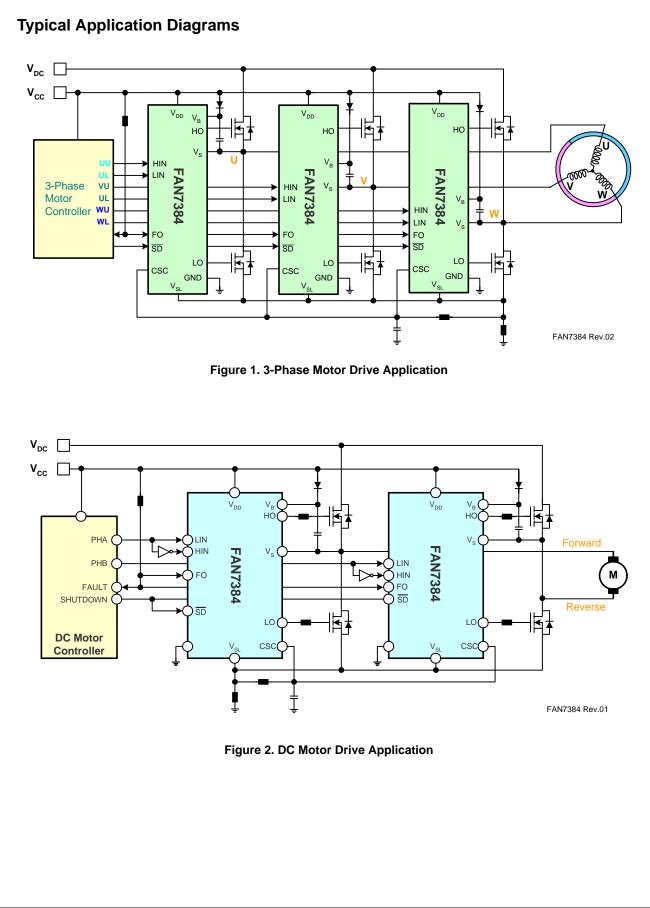
14-SOP

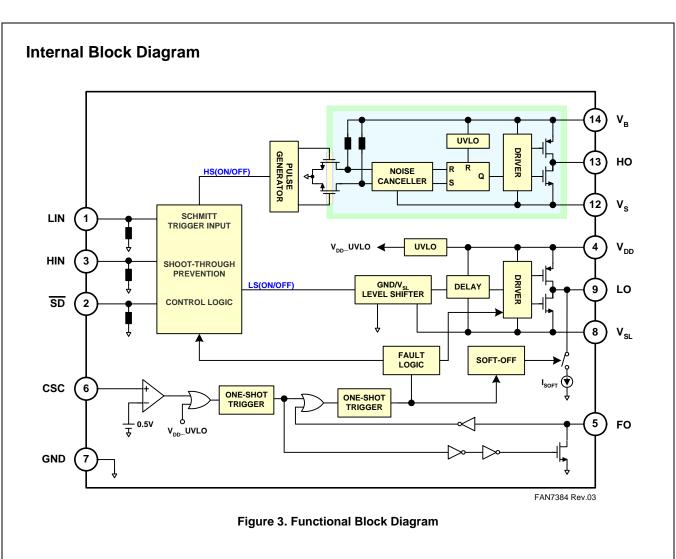


### **Ordering Information**

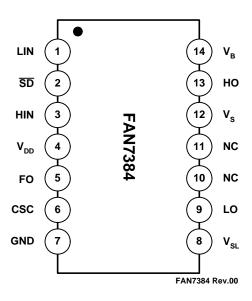
Part Number	Package	Pb-Free	Operating Temperature Range	Packing Method
FAN7384M	14-SOP	Yes	-40°C ~ 125°C	Tube
FAN7384MX	14-30F	105	-40 0 ~ 125 0	Tape & Reel

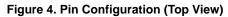
November 2006





# **Pin Configuration**





### **Pin Definitions**

Pin #	Name	Description	
1	LIN	Logic Input for low-side gate driver	
2	SD	Shutdown control input with active low	
3	HIN	Logic Input for high-side gate driver	
4	V <sub>DD</sub>	Low-side power supply voltage	
5	FO	Bi-direction fault pin with open drain	
6	CSC	Short-circuit current detection input	
7	GND	Ground	
8	V <sub>SL</sub>	Low-side supply offset voltage	
9	LO	Low-side gate driver output	
10	NC	No connection	
11	NC	No connection	
12	V <sub>S</sub>	High-side floating supply offset voltage	
13	HO	High-side gate driver output	
14	VB	High-side floating supply voltage	

# **Absolute Maximum Ratings**

The "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. The device should not be operated at these limits. The parametric values defined in the Electrical Characteristics tables are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table defines the conditions for actual device operation.  $T_A=25$ °C, unless otherwise specified.

Symbol	Parameter	Min.	Max.	Unit
V <sub>S</sub>	High-side offset voltage V <sub>S</sub>	V <sub>B</sub> -25	V <sub>B</sub> +0.3	V
V <sub>B</sub>	V <sub>B</sub> High-side floating supply voltage V <sub>B</sub>		625	V
V <sub>HO</sub>	High-side floating output voltage	V <sub>S</sub> -0.3	V <sub>B</sub> +0.3	V
V <sub>DD</sub>	Low-side and logic-fixed supply voltage	-0.3	25	V
V <sub>IN</sub>	Logic input voltage (HIN, LIN, SD)	-0.3	V <sub>DD</sub> +0.3	V
V <sub>CSC</sub>	Current sense input voltage	-0.3	V <sub>DD</sub> +0.3	V
V <sub>FO</sub>	Fault output voltage	-0.3	V <sub>DD</sub> +0.3	V
dV <sub>S</sub> /dt	Allowable offset voltage slew rate		50	V/ns
P <sub>D</sub> <sup>(1)(2)(3)</sup>	Power dissipation		1.0	W
$\theta_{JA}$	Thermal resistance, junction-to-ambient		110	°C/W
TJ	Junction temperature		150	°C
Τ <sub>S</sub>	Storage temperature	-55	150	°C

#### Notes:

1. Mounted on 76.2 x 114.3 x 1.6mm PCB (FR-4 glass epoxy material).

2. Refer to the following standards:

JESD51-2: Integral circuits thermal test method environmental conditions - natural convection JESD51-3: Low effective thermal conductivity test board for leaded surface mount packages

3. Do not exceed P<sub>D</sub> under any circumstances.

### **Recommended Operating Conditions**

Symbol Parameter		Condition	Min.	Max.	Unit	
VB	High-side floating supply voltage		V <sub>S</sub> +13	V <sub>S</sub> +20	V	
VS	High-side floating supply offset voltage		6-V <sub>DD</sub>	600	V	
V <sub>DD</sub>	supply voltage		13	20	V	
V <sub>HO</sub>	High-side output voltage		Vs	VB	V	
V <sub>LO</sub>	Low-side output voltage		GND	V <sub>DD</sub>	V	
V <sub>IN</sub> Logic input voltage (HIN, LIN, SD)			GND	V <sub>DD</sub>	V	
V <sub>FO</sub>	Fault output voltage		-0.3	V <sub>DD</sub> +0.3	V	
T <sub>A</sub>	Ambient temperature		-40	125	°C	

# **Electrical Characteristics**

 $V_{BIAS}$  ( $V_{DD}$ ,  $V_{BS}$ ) = 15.0V,  $T_A$  = 25°C, unless otherwise specified. The  $V_{IN}$  and  $I_{IN}$  parameters are referenced to GND. The  $V_O$  and  $I_O$  parameters are referenced to GND and  $V_S$  is applicable to HO and LO.

Symbol	Characteristics	Condition	Min.	Тур.	Max.	Unit
LOW SIDE	E POWER SUPPLY SECTION					
I <sub>QDD</sub>	Quiescent V <sub>DD</sub> supply current	V <sub>LIN</sub> =0V or 5V		600	800	μΑ
I <sub>PDD</sub>	Operating V <sub>DD</sub> supply current	f <sub>LIN</sub> =20kHz, rms value		950	1300	μΑ
V <sub>DDUV+</sub>	V <sub>DD</sub> supply under-voltage positive going threshold	V <sub>DD</sub> =Sweep	10.9	11.9	12.9	V
V <sub>DDUV-</sub>	V <sub>DD</sub> supply under-voltage negative going threshold	V <sub>DD</sub> =Sweep	10.4	11.4	12.4	V
V <sub>DDHYS</sub>	V <sub>DD</sub> supply under-voltage lockout hysteresis	V <sub>DD</sub> =Sweep		0.5		V
BOOTSTR	RAPPED POWER SUPPLY SECTION					
V <sub>BSUV+</sub>	V <sub>BS</sub> supply under-voltage positive going threshold	V <sub>BS</sub> =Sweep	10.6	11.5	12.4	V
V <sub>BSUV-</sub>	V <sub>BS</sub> supply under-voltage negative going threshold	V <sub>BS</sub> =Sweep	10.1	11.0	11.9	V
V <sub>BSHYS</sub>	V <sub>BS</sub> supply under-voltage lockout hysteresis	V <sub>BS</sub> =Sweep		0.5		V
I <sub>LK</sub>	Offset supply leakage current	V <sub>B</sub> =V <sub>S</sub> =600V			10	μΑ
I <sub>QBS</sub>	Quiescent V <sub>BS</sub> supply current	V <sub>HIN</sub> =0V or 5V		50	90	μΑ
I <sub>PBS</sub>	Operating V <sub>BS</sub> supply current	f <sub>HIN</sub> =20kHz, rms value		400	600	μΑ
GATE DR	IVER OUTPUT SECTION					
V <sub>OH</sub>	High-level output voltage, $V_{BIAS}$ - $V_{O}$	I <sub>O</sub> =0mA (No Load)			100	mV
V <sub>OL</sub>	Low-level output voltage, V <sub>O</sub>	I <sub>O</sub> =0mA (No Load)			100	mV
I <sub>O+</sub>	Output HIGH short-circuit pulse current	$V_{O}$ =0V, $V_{IN}$ =5V with PW<10µs	200	250		mA
I <sub>O-</sub>	Output LOW short-circuit pulsed current	$V_{O}\text{=}15V,V_{IN}\text{=}0V$ with PW<10 $\mu\text{s}$	420	500		mA
VS	Allowable negative $\rm V_S$ pin voltage for IN signal propagation to $\rm H_O$			-9.8	-7.0	V
V <sub>SL</sub> -GND	$V_{SL}$ -GND/GND- $V_{SL}$ voltage educability		-7.0		7.0	V
SHUTDO	WN CONTROL SECTION (SD)					
SD+	Shutdown "1" input voltage				1.2	V
SD-	Shutdown "0" input voltage		2.5			V
LOGIC IN	PUT SECTION (HIN, LIN)					
V <sub>IH</sub>	Logic "1" input voltage		2.5			V
V <sub>IL</sub>	Logic "0" input voltage				1.2	V
V <sub>INHYS</sub>	Logic input hysteresis voltage			0.5		V
I <sub>IN+</sub>	Logic "1" input bias current	V <sub>IN</sub> =5V	10	15	20	μΑ
I <sub>IN-</sub>	Logic "0" input bias current	V <sub>IN</sub> =0V			2.0	μΑ

### Electrical Characteristics (Continued)

 $V_{BIAS}$  ( $V_{DD}$ ,  $V_{BS}$ ) = 15.0V,  $T_A$  = 25°C, unless otherwise specified. The  $V_{IN}$  and  $I_{IN}$  parameters are referenced to GND. The  $V_O$  and  $I_O$  parameters are referenced to GND and  $V_S$  is applicable to HO and LO.

Symbol	Characteristics	Condition	Min.	Тур.	Max.	Unit
SHORT-C	IRCUIT PROTECTION					
V <sub>CSCREF</sub>	F Short-circuit detector reference voltage		0.47	0.50	0.53	V
I <sub>CSCIN</sub>	Short-circuit input current	$V_{CSCIN}=1V, R_{CSCIN}=100K\Omega$	5	10	15	μA
I <sub>SOFT</sub>	Soft turn-off source current	V <sub>DD</sub> =15V	5	10	15	mA
-V <sub>CSC</sub>	Negative CSC pin immunity <sup>(4)</sup>	Voltage on CSC pin up to -12V, Time<2µs			-20	V
FAULT DE	ETECTION SECTION					
V <sub>FINH</sub>	Fault input high level voltage		2.5			V
V <sub>FINL</sub> Fault input low level voltage					1.2	V
V <sub>FINHYS</sub>	Fault input hysteresis voltage <sup>(4)</sup>			0.5		V
V <sub>FOH</sub>	Fault output high level voltage	V <sub>CSC</sub> =0V, R <sub>PULL-UP</sub> =4.7KΩ	4.7			V
V <sub>FOL</sub>	Fault output low level voltage	V <sub>CSC</sub> =1V, I <sub>FO</sub> =2mA			0.8	V
V <sub>FOWD</sub>	Fault output pulse width	V <sub>CSCIN</sub> =1V		60	100	µsec

#### Note:

4. These parameter, although guaranteed, not 100% tested in production.

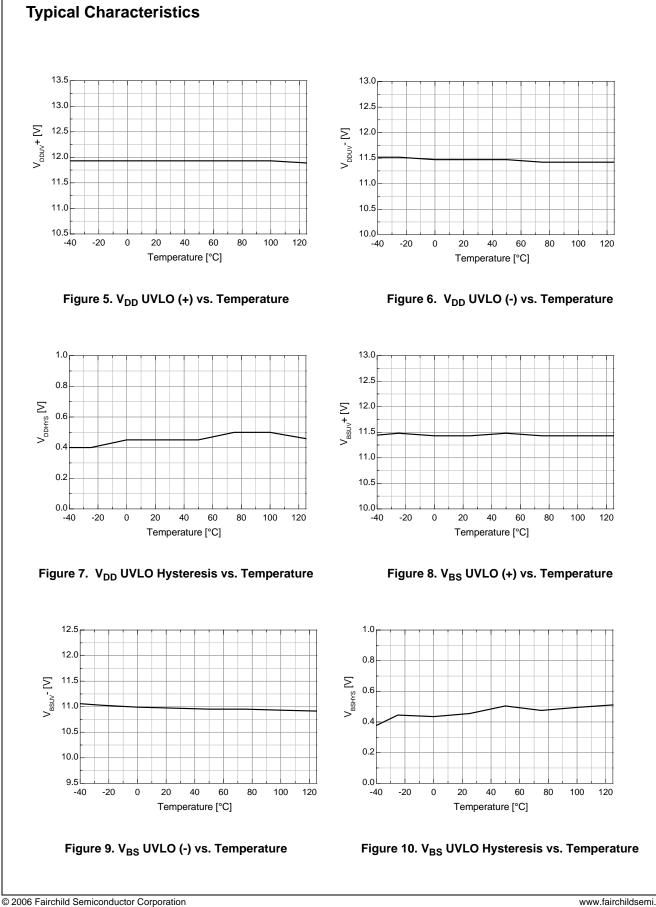
## **Dynamic Electrical Characteristics**

 $T_A=25^{\circ}C$ ,  $V_{BIAS}$  ( $V_{DD}$ ,  $V_{BS}$ ) = 15.0V,  $V_S$  = GND,  $C_{Load}$  = 1000pF unless otherwise specified.

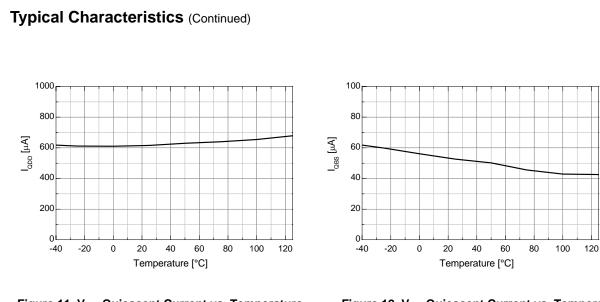
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
t <sub>on</sub>	Turn-on propagation delay	V <sub>S</sub> =0V		180	260	ns
t <sub>off</sub>	Turn-off propagation delay	V <sub>S</sub> =0V		170	240	ns
t <sub>r</sub>	Turn-on rise time			50	100	ns
t <sub>f</sub>	Turn-off fall time			30	80	ns
MT	Delay matching				50	ns
DT	Dead-time		80	120	170	ns
t <sub>UVFLT</sub>	Under-voltage filtering time <sup>(5)</sup>			16		µsec
t <sub>CSCFLT</sub>	CSC pin filtering time <sup>(5)</sup>			300		ns
t <sub>CSCFO</sub>	Time from CSC triggering to FO <sup>(5)</sup>			350		ns
tcsclo	Time from CSC triggering to low-side gate $output^{(5)}$	From V <sub>CSC</sub> =1V to starting gate turn-off		600		ns
t <sub>SDFO</sub>	Shutdown to FO propagation delay <sup>(5)</sup>			60		ns
t <sub>SDOFF</sub>	Shutdown to HIGH/LOW-side gate off <sup>(5)</sup>			100		ns

#### Note:

5. These parameter, although guaranteed, not 100% tested in production.



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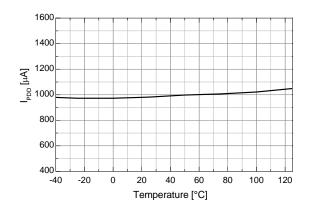


Figure 13. V<sub>DD</sub> Operating Current vs. Temperature

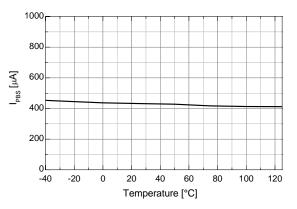
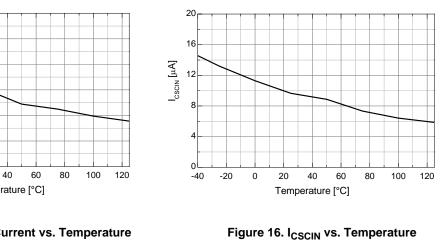


Figure 14. V<sub>BS</sub> Operating Current vs. Temperature



Temperature [°C] Figure 15. Logic Input Current vs. Temperature

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0

20

30

25

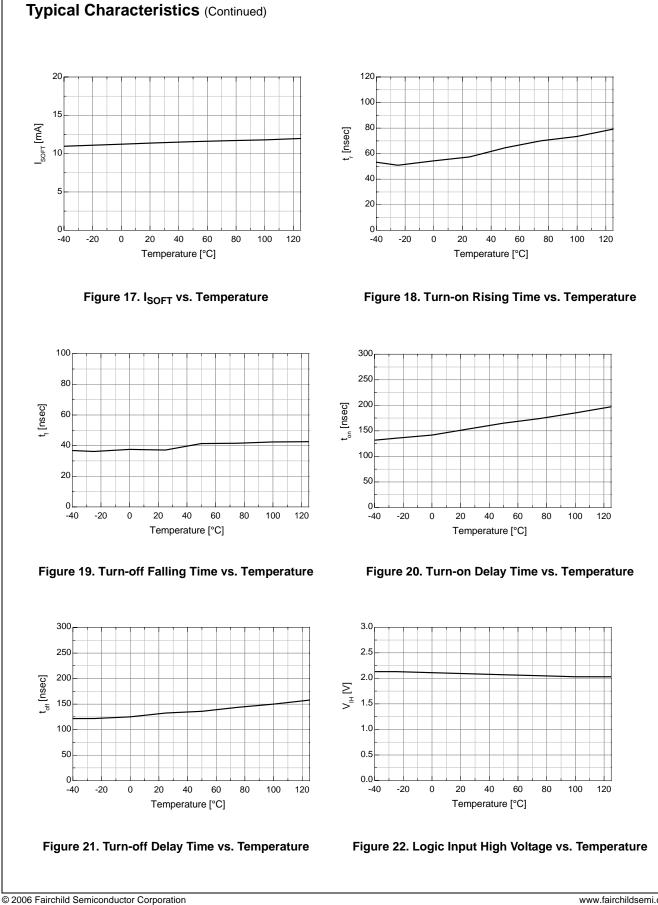
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-40

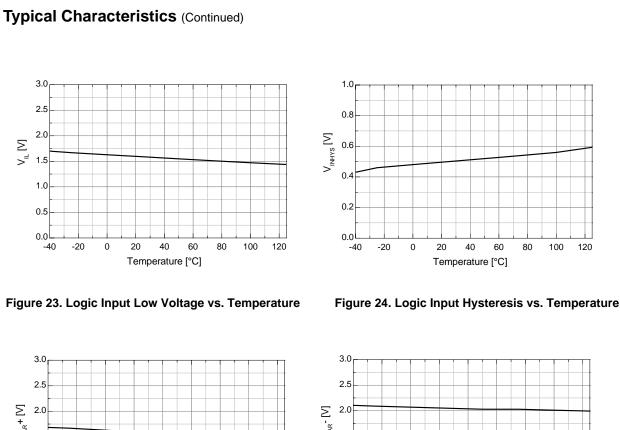
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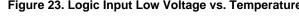
FAN7384 Half-Bridge Gate-Drive IC

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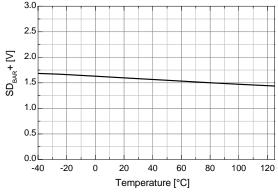


Figure 25. SD Positive Threshold vs. Temperature

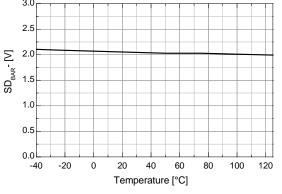
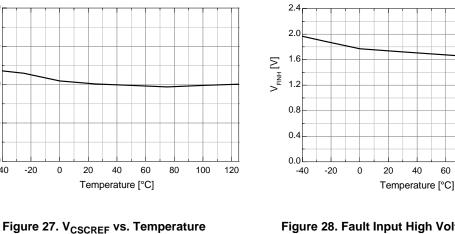
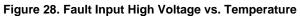


Figure 26. SD Negative Threshold vs. Temperature





60

100

80

120

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-20

0

20

0.60

0.55

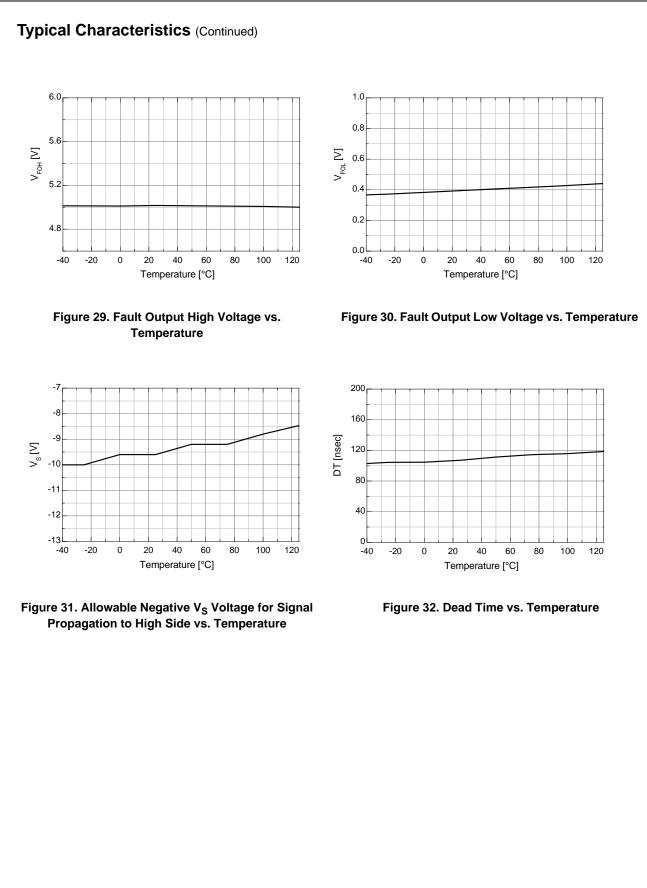
0.50

0.45

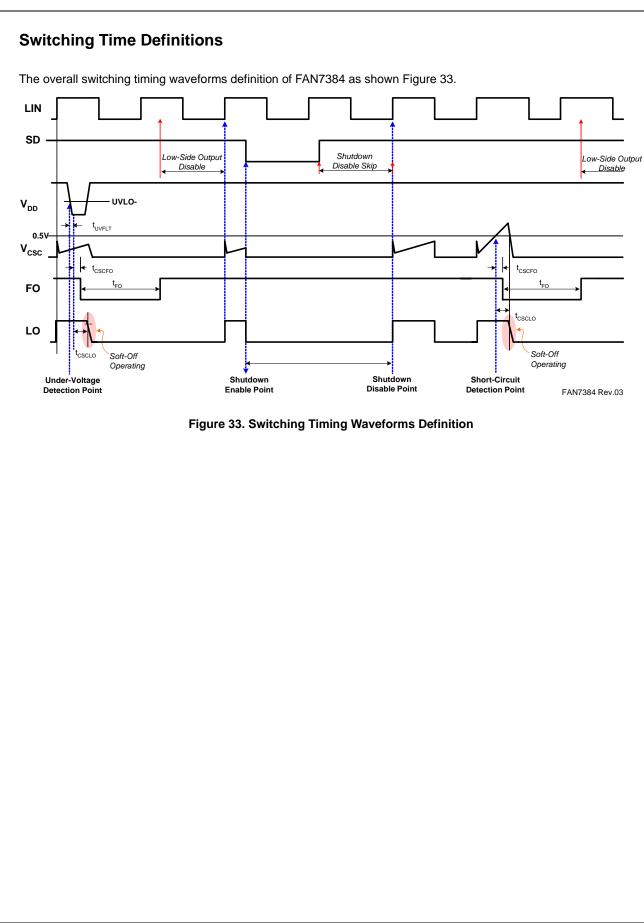
0.40

-40

V<sub>CSCREF</sub> [V]







### **Typical Application Information**

#### **1. Protection Function**

#### 1.1 Under-Voltage Lockout (UVLO)

The high- and low-side drivers include under-voltage lockout (UVLO) protection circuitry that monitors the supply voltage ( $V_{DD}$ ) and bootstrap capacitor voltage ( $V_{BS}$ ) independently. It can be designed to prevent malfunction when  $V_{DD}$  and  $V_{BS}$  are lower than the specified threshold voltage. Moreover, the UVLO hysteresis prevents chattering during power supply transitions. If the supply voltage ( $V_{DD}$ ) maintains an under-voltage condition over under-voltage filtering times (typically 16µs), the fault and soft-off circuits are activated, as shown Figure 34.

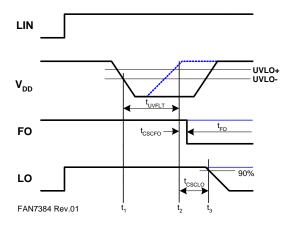


Figure 34. Waveforms for Under-Voltage Lockout

#### **1.2 Shoot-Through Prevention Function**

The FAN7384 has a shoot-through prevention circuitry that monitors the high- and low-side inputs. It can be designed to prevent outputs of high- and low-side turning on at same time, as shown Figure 35 and 36.

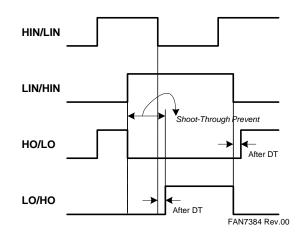
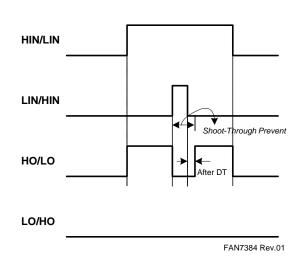


Figure 35. Waveforms for Shoot-Through Prevention



#### Figure 36. Waveforms for Shoot-Through Prevention

#### **1.3 Over-Current Protection Function**

The FAN7384 has over-current detection circuitry that monitors the current-by-current sensing resistor connected from the low-side switch source ( $V_{SL}$ ) to ground.

It is a built-in time-filler from the over-current event to prevent malfunction from a noise source, such as leading-edge pulse in inductive load application, as shown Figure 37.

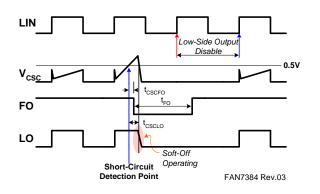
The sensing current is calculated as follows:

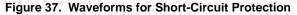
$$I_{\rm CS} = \frac{V_{\rm CSCREF}}{R_{\rm CS}} [A] \tag{1}$$

where,

V<sub>CSCREF</sub>: Reference voltage of current sense comparator

R<sub>CS</sub>: Current sensing resistor





### 2. Layout Considerations

For optimum performance, considerations must be taken during printed circuit board (PCB) layout.

#### 2.1 Supply Capacitors

If the output stages are able to quickly turn on a switching device with a high value of current, the supply capacitors must be placed as close as possible to the device pins (V<sub>DD</sub> and GND for the ground-tied supply, V<sub>B</sub> and V<sub>S</sub> for the floating supply) to minimize parasitic inductance and resistance.

#### 2.2 Gate-Drive Loop

Current loops behave like antennae, able to receive and transmit noise. To reduce the noise coupling/emission and improve the power switch turn-on and off performance, gate-drive loops must be reduced as much as possible.

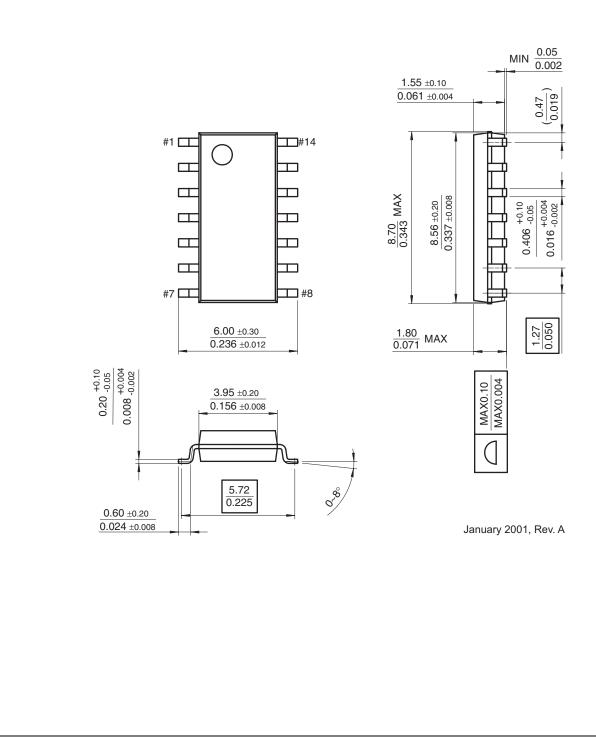
#### 2.3 Ground Plane

To minimize noise coupling, the ground plane should not be placed under or near the high-voltage floating side.

# **Package Dimensions**

### 14-SOP

Dimensions are in millimeters unless otherwise noted.



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Datasheet Identification	Product Status	Definition			
Advance Information Formative or In Design		This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.			
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No Identification Needed	Identification Needed Full Production This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any without notice to improve design.				
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